

2811
PATENT

Case Docket No. MICRON.009071

Date: July 23, 2001

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In re application of : Schuegraf et al.
App. No. : 08/932,228
Filed : September 17, 1997
For : SHALLOW TRENCH
ISOLATION USING LOW
DIELECTRIC CONSTANT
INSULATOR
Examiner : Hung Vu
Art Unit : 2811

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Assistant Commissioner for Patents, Washington, D.C.
20231, on

July 23, 2001

(Date)
Adeel Syed Akhtar
Adeel S. Akhtar, Reg. No. 41,394

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

Sir:

Transmitted herewith is an amendment in the above-identified application.

- (X) A Request for Reconsideration in 5 pages.
- (X) Please charge any additional fees, including any fees for additional extension of time, or credit overpayment to Deposit Account No. 11-1410.
- (X) Return prepaid postcard.

Adeel Syed Akhtar
Adeel S. Akhtar
Registration No. 41,394
Attorney of Record



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Applicant	:	Schuegraf et al.)	Group Art Unit 2811
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)	
Examiner	:	Hung Vu)	

#22
Req for
Reconsideration
FJONES
8-1-01

REQUEST FOR RECONSIDERATION

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Final Office Action, mailed June 5, 2001, Applicants respectfully request reconsideration of the application in view of the comments below.

REMARKS

The Examiner has continued to reject the claims in view of prior art. Applicants respectfully traverse the rejections and submit that the Examiner is unjustifiably ignoring claim language.

Rejections Under 35 U.S.C. Section 102 (a)

The Examiner has rejected Claims 21, 22 and 24 as being anticipated by Anjum et al. (U.S. Patent No. 5,372,951). Anjum et al. taught formation of a halide-doped silicon oxide by a thermal oxidation process, or a LoCal Oxidation of Silicon (LOCOS) process. Consequently, the final structure of Anjum et al. is readily recognized as a product of such a process due to the characteristic bird's beak structure inevitably produced by the process of Anjum et al. See Figure 5 of Anjum et al.